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IXYS Introduces 650V New Ultra Junction X2-Class Power MOSFETs A Better Technology than Super Junction FETs

Leiden, Netherlands and Milpitas, CA. August 27, 2015 – IXYS Corporation (NASDAQ: IXYS), a worldwide manufacturer of power semiconductors and ICs for energy efficiency, power management, medical, transportation and motor control applications today announced its Ultra Junction Power MOSFET product line: 650V X2-Class Power MOSFETs. With current ratings ranging from 2A to 120A, and on resistance as low as 24 milliohms, they are well suited for high-efficiency, high-speed power switching applications.

These devices were developed using a charge compensation principle and proprietary process technology, resulting in Power MOSFETs with significantly reduced on resistance and gate charge. A low on-state resistance reduces the conduction losses. It also lowers the energy stored in the output capacitance, thereby minimizing the switching losses. A low gate charge results in higher efficiency at light loads as well as lower gate drive requirements. In addition, these MOSFETs are avalanche rated and exhibit a superior dv/dt performance. Also due to the positive temperature coefficient of their on-state resistance, they can be operated in parallel to meet higher current requirements.

"Our Ultra Junction technology has a better figure of merit than the state of the art super junction technology, when it comes to power MOSFET performance and cost of manufacturing. Our scientists have developed it with IXYS' standards of ruggedness that made our power MOSFETs world famous. With the combination of reduced on resistance and improved switching and thermal performance, these devices offer the best cost performance to our customers, even better than SiC MOSFETs, especially in ruggedness and reliability," commented Dr. Nathan Zommer, CEO and Founder of IXYS Corporation. "We have already been delivering these products to select customers and utilize them in our new Power Solid State Relay products."

Designed for such applications as Power Factor Correction (PFC) circuits, switched-mode and resonant-mode power supplies, DC-DC converters, AC and DC motor drives, solid state relays, and robotic and servo control, these MOSFETs enable higher efficiency along with high power density and cooler system performance.

These new 650V X2 Power MOSFETs are available in the following international standard size packages: TO-252, TO-220 (standard or over-molded), TO-263, SOT-227, TO-247, PLUS247,

and TO-264. Some example part numbers include IXTY2N65X2, IXTA4N65X2, IXTP8N65X2, and IXTK102N65X2, with drain current ratings of 2A, 4A, 8A, and 102A, respectively.

Additional product information can be obtained by visiting the IXYS website at http://www.ixys.com or by contacting the company directly.

About IXYS Corporation

IXYS Corporation makes and markets technology-driven products to improve power conversion efficiency, generate solar and wind power, and provide efficient motor control for industrial applications. IXYS offers a diversified product base that addresses worldwide needs for power control, electrical efficiency, renewable energy, telecommunications, medical devices, electronic displays, and RF power.

Safe Harbor Statement

Any statements contained in this press release that are not statements of historical fact, including the performance, rating, benefits, reliability, availability and suitability of products for various applications, may be deemed to be forward-looking statements. There are a number of important factors that could cause the results of IXYS to differ materially from those indicated by these forward-looking statements, including, among others, risks detailed from time to time in the Company's SEC reports, including its Annual Report on Form 10-Q for the fiscal quarter ended June 30, 2015. The Company undertakes no obligation to publicly release the results of any revisions to these forward-looking statements.